

**22N25-HC**

Preliminary

Power MOSFET**22A, 250V N-CHANNEL
POWER MOSFET****DESCRIPTION**

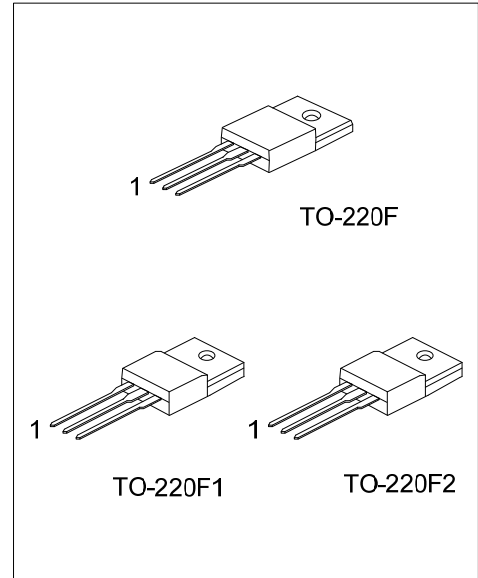
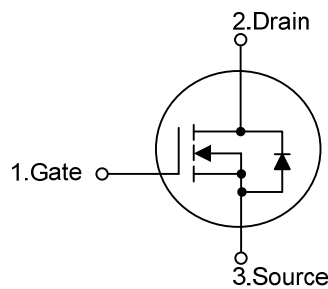
The UTC **22N25-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **22N25-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

FEATURES

* $R_{DS(ON)} \leq 0.18 \Omega$ @ $V_{GS}=10V$, $I_D=11A$

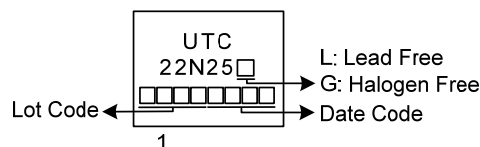
* High Switching Speed

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
22N25L-TF1-T	22N25G-TF1-T	TO-220F1	G	D	S	Tube
22N25L-TF2-T	22N25G-TF2-T	TO-220F2	G	D	S	Tube
22N25L-TF3-T	22N25G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

22N25G-TF1-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube (2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F (3) G: Halogen Free and Lead Free, L: Lead Free
--	---

MARKING

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	250	V
Gate-Source Voltage		V_{GS}	± 30	V
Continuous Drain Current	Continuous	I_D	22	A
	Pulsed	I_{DM}	44	A
Single Pulsed Avalanche Current		I_{AS}	5.7	A
Single Pulsed Avalanche Energy		E_{AS}	504.3	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.75	V/ns
Power Dissipation		P_D	57	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=5.7\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 22\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	110	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.19 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

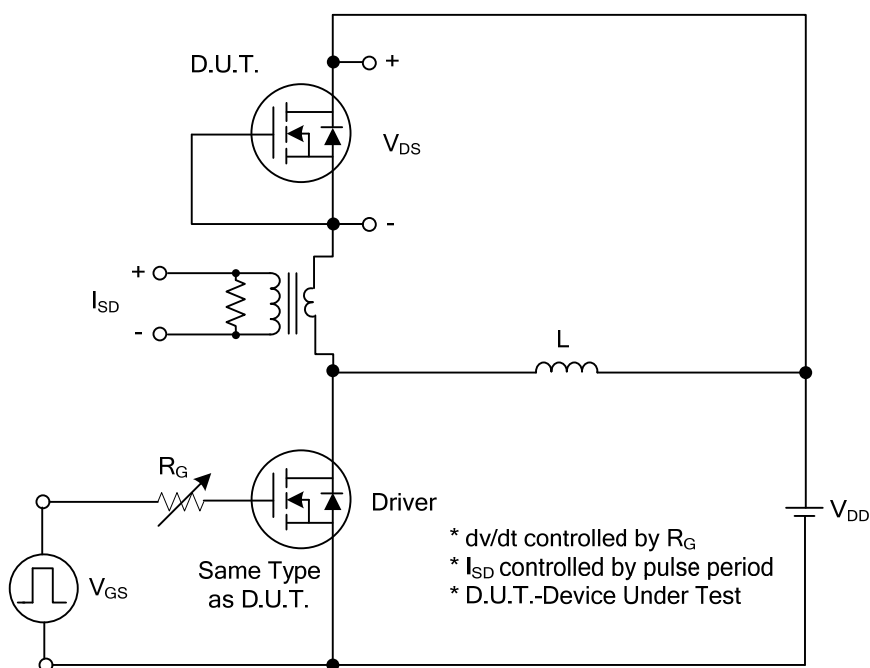
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	250			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =250V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =11A			0.18	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		1012		pF
Output Capacitance		C _{OSS}			160.4		pF
Reverse Transfer Capacitance		C _{RSS}			8.8		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DS} =200V, V _{GS} =10V, I _D =22A I _G =1mA (Note 1, 2)		26.4		nC
Gate to Source Charge		Q _{GS}			8.4		nC
Gate to Drain Charge		Q _{GD}			6.6		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =22A, R _G =25Ω (Note 1, 2)		9.4		ns
Rise Time		t _R			18.2		ns
Turn-OFF Delay Time		t _{D(OFF)}			59.7		ns
Fall-Time		t _F			23.5		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				22	A
Maximum Body-Diode Pulsed Current		I _{SM}				44	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =22A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =22A, V _{GS} =0V,		141.3		ns
Reverse Recovery Charge		Q _{rr}	dI _F /dt=100A/μs (Note 1)		1.4		μC

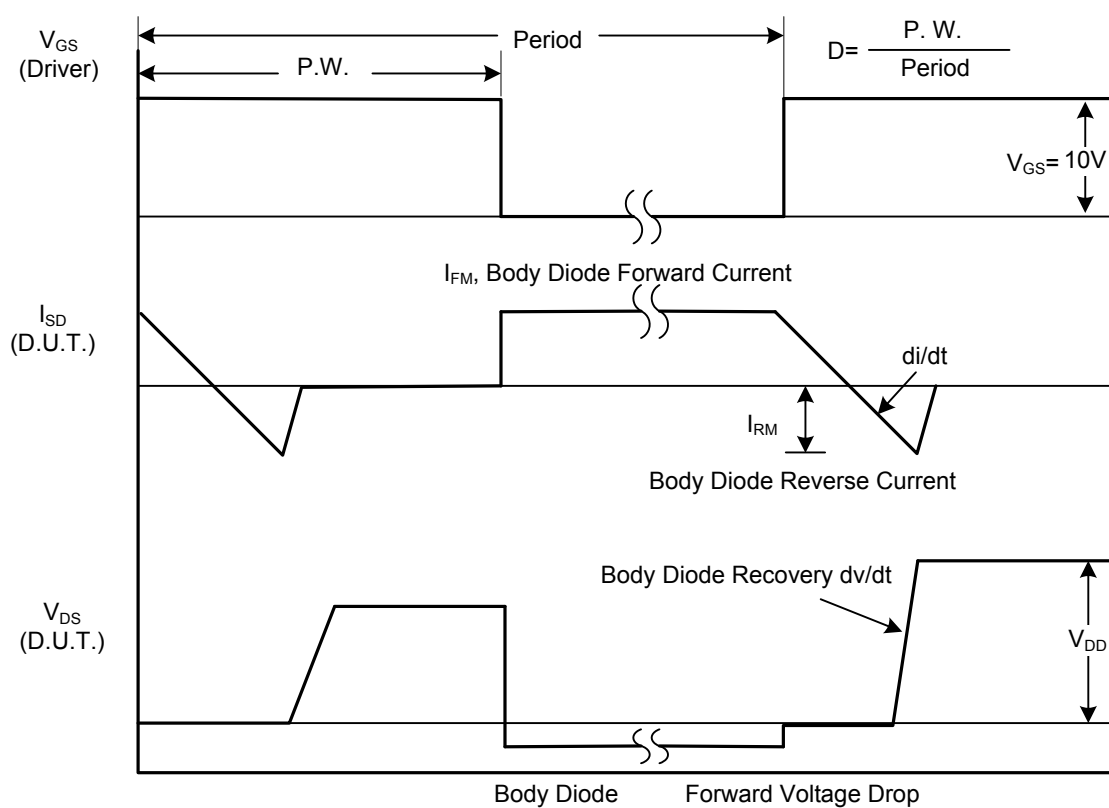
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

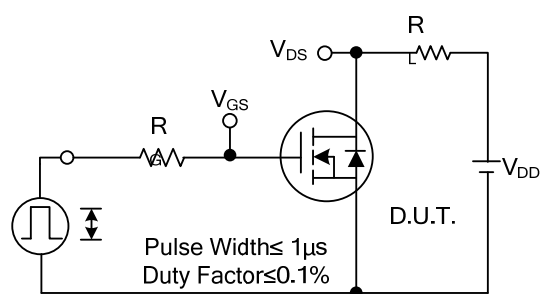


Peak Diode Recovery dv/dt Test Circuit

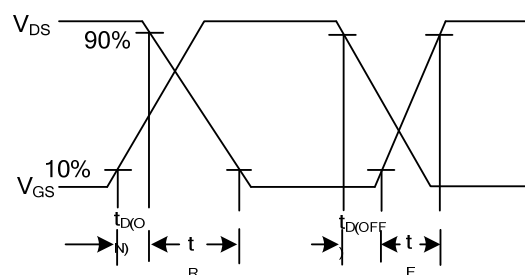


Peak Diode Recovery dv/dt Waveforms

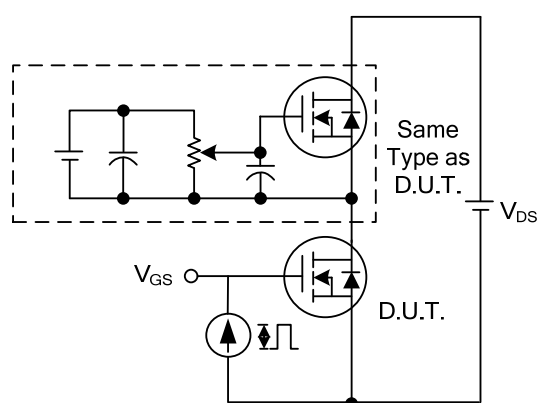
■ TEST CIRCUITS AND WAVEFORMS



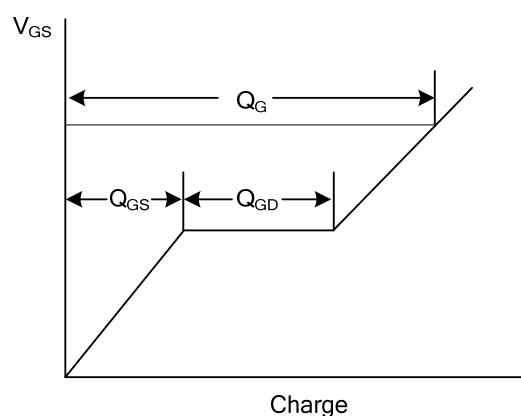
Switching Test Circuit



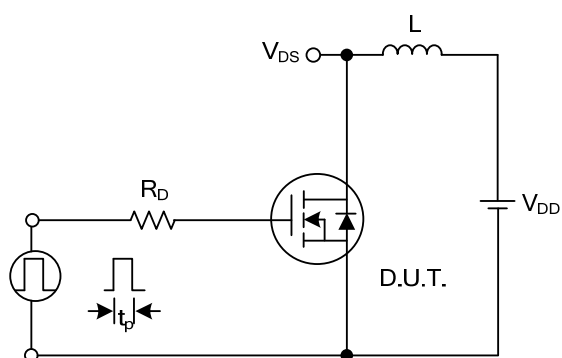
Switching Waveforms



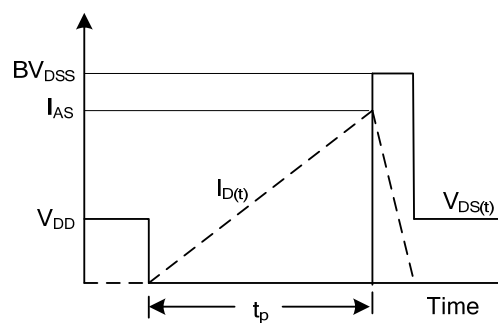
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.